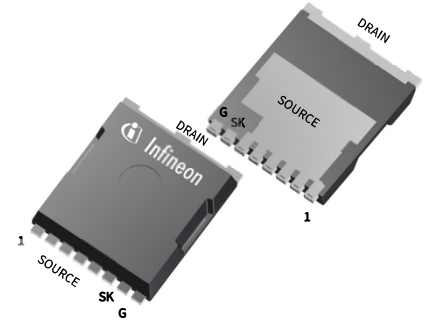


IGT60R070D1

600V CoolGaN™ enhancement-mode Power Transistor

Features

- Enhancement mode transistor – Normally OFF switch
- Ultra fast switching
- No reverse-recovery charge
- Capable of reverse conduction
- Low gate charge, low output charge
- Superior commutation ruggedness
- Qualified for industrial applications according to JEDEC Standards (JESD47 and JESD22)



Benefits

- Improves system efficiency
- Improves power density
- Enables higher operating frequency
- System cost reduction savings
- Reduces EMI

Gate	8
Drain	drain contact
Kelvin Source	7
Source	1,2,3,4,5,6

Applications

PFC stages, hard switching PWM stages and resonant switching stages for Server and Telecom SMPS, UPS, Industrial Battery chargers and high performance SMPS

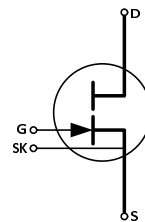


Table 1 Key Performance Parameters at T_j = 25 °C

Parameter	Value	Unit
V _{DS,max}	600	V
R _{DS(on),max}	70	mΩ
Q _{G,typ}	5.8	nC
I _{D,pulse}	60	A
Q _{oss @ 400 V}	41	nC
Q _{rr}	0	nC



Table 2 Ordering Information

Type / Ordering Code	Package	Marking	Related links
IGT60R070D1	PG-HSOF-8	60R070D1	NA



Table of Contents

Features	1
Benefits	1
Applications.....	1
Table of Contents	2
1 Maximum ratings	3
2 Thermal characteristics	4
3 Electrical characteristics	5
4 Electrical characteristics diagrams	7
5 Test Circuits	13
6 Package Outlines	14
7 Revision History	15

1 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Continuous application of maximum ratings can deteriorate transistor lifetime. For further information, contact your local Infineon sales office.

Table 3 Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Drain Source Voltage ¹	$V_{DS,max}$	-	-	600	V	$V_{GS} = 0\text{ V}$
Continuous current, drain source	I_D	-	-	31	A	$T_C = 25\text{ °C}; T_j = T_{j,max}$
		-	-	20		$T_C = 100\text{ °C}; T_j = T_{j,max}$
		-	-	14		$T_C = 125\text{ °C}; T_j = T_{j,max}$
Pulsed current, drain source ^{2 3}	$I_{D,pulse}$	-	-	60	A	$T_C = 25\text{ °C}; I_G = 26.1\text{ mA}$; See Figure 3; Figure 21;
Pulsed current, drain source ^{3 4}	$I_{D,pulse}$	-	-	35	A	$T_C = 125\text{ °C}; I_G = 26.1\text{ mA}$; See Figure 4; Figure 22;
Gate current, continuous ^{4 5}	I_G	-	-	20	mA	$T_j = -55\text{ °C}$ to 150 °C ; Refer to gate drive app note
Gate current, pulsed ⁵	$I_{G,pulse}$	-	-	2000	mA	$T_j = -55\text{ °C}$ to 150 °C ; $t_{PULSE} = 50\text{ ns}$, $f = 100\text{ kHz}$ Refer to gate drive app note
Gate source voltage, continuous ⁵	V_{GS}	-10	-	-	V	$T_j = -55\text{ °C}$ to 150 °C ; Refer to gate drive app note
Gate source voltage, pulsed ⁵	$V_{GS,pulse}$	-25	-	-	V	$T_j = -55\text{ °C}$ to 150 °C ; $t_{PULSE} = 50\text{ ns}$, $f = 100\text{ kHz}$; open drain Refer to gate drive app note
Power dissipation	P_{tot}	-	-	125	W	$T_C = 25\text{ °C}$
Operating temperature	T_j	-55	-	150	°C	
Storage temperature	T_{stg}	-55	-	150	°C	Max shelf life depends on storage conditions.
Drain-source voltage slew-rate	dV/dt			200	V/ns	

¹ All devices are 100% tested at $I_{DS} = 12.2\text{ mA}$ to assure $V_{DS} \geq 800\text{ V}$

² Limits derived from product characterization, parameter not measured during production

³ Ensure that average gate drive current, I_G is $\leq 20\text{ mA}$

⁴ Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

⁵ We recommend using an advanced driving technique to optimize the device performance. Please see application information for details.

2 Thermal characteristics

Table 4 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	R_{thJC}	-	-	1	°C/W	
Thermal resistance, junction-ambient	R_{thJA}	-	-	62	°C/W	Device on PCB, minimum footprint
Thermal resistance, junction-ambient for SMD version	R_{thJA}	-	35	45	°C/W	Device on 40mm*40mm* 1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Reflow soldering temperature	T_{sold}	-	-	245	°C	MSL3

3 Electrical characteristics

at $T_j = 25\text{ °C}$, unless specified otherwise

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate threshold voltage	$V_{GS(th)}$	0.9 0.7	1.2 1.0	1.6 1.4	V	$I_{DS} = 2.6\text{ mA}; V_{DS} = 10\text{ V}; T_j = 25\text{ °C}$ $I_{DS} = 2.6\text{ mA}; V_{DS} = 10\text{ V}; T_j = 125\text{ °C}$
Drain-Source leakage current	I_{DSS}	- -	1 20	100 -	μA	$V_{DS} = 600\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ °C}$ $V_{DS} = 600\text{ V}; V_{GS} = 0\text{ V}; T_j = 150\text{ °C}$
Drain-Source leakage current at application conditions ¹	I_{DSSapp}	-	60	-	μA	$V_{DS} = 400\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$
Gate-Source leakage current	I_{GSS}	-1 -1	- -	- -	mA	$V_{DS} = 0\text{ V}; V_{GS} = -10\text{ V}; T_j = 25\text{ °C}$ $V_{DS} = 0\text{ V}; V_{GS} = -10\text{ V}; T_j = 125\text{ °C}$
Drain-Source on-state resistance	$R_{DS(on)}$	- -	0.055 0.100	0.070 -	Ω	$I_G = 26.1\text{ mA}; I_D = 8\text{ A}; T_j = 25\text{ °C}$ $I_G = 26.1\text{ mA}; I_D = 8\text{ A}; T_j = 150\text{ °C}$
Gate resistance	$R_{G,int}$	-	0.78	-	Ω	LCR impedance measurement; $f = f_{res}$; open drain;

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	380	-	pF	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$ $f = 1\text{ MHz}$
Output capacitance	C_{oss}	-	72	-	pF	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$ $f = 1\text{ MHz}$
Reverse Transfer capacitance	C_{rss}	-	0.3	-	pF	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V};$ $f = 1\text{ MHz}$
Effective output capacitance, energy related ²	$C_{o(er)}$	-	80	-	pF	$V_{DS} = 0\text{ to }400\text{ V}$
Effective output capacitance, time related ³	$C_{o(tr)}$	-	102.5	-	pF	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V};$ $I_D = \text{const}$
Output charge	Q_{oss}	-	41	-	nC	$V_{DS} = 0\text{ to }400\text{ V}$
Turn- on delay time	$t_{d(on)}$	-	12	-	ns	see Figure 23
Turn- off delay time	$t_{d(off)}$	-	13	-	ns	see Figure 23
Rise time	t_r	-	8	-	ns	see Figure 23
Fall time	t_f	-	13	-	ns	see Figure 23

¹ Parameter represents end of use leakage in applications

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V

³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V

Table 7 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Gate charge	Q_G	-	5.8	-	nC	$I_{GS} = 0$ to 10 mA; $V_{DS} = 400$ V; $I_D = 8$ A

Table 8 Reverse conduction characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Source-Drain reverse voltage	V_{SD}	-	2.0	2.5	V	$V_{GS} = 0$ V; $I_{SD} = 8$ A
Pulsed current, reverse	$I_{S,pulse}$	-	-	60	A	$I_G = 26.1$ mA
Reverse recovery charge	Q_{rr}^1	-	0	-	nC	$I_S = 8$ A, $V_{DS} = 400$ V
Reverse recovery time	t_{rr}	-	0	-	ns	
Peak reverse recovery current	I_{rrm}	-	0	-	A	

4 Electrical characteristics diagrams

at $T_j = 25\text{ }^\circ\text{C}$, unless specified otherwise

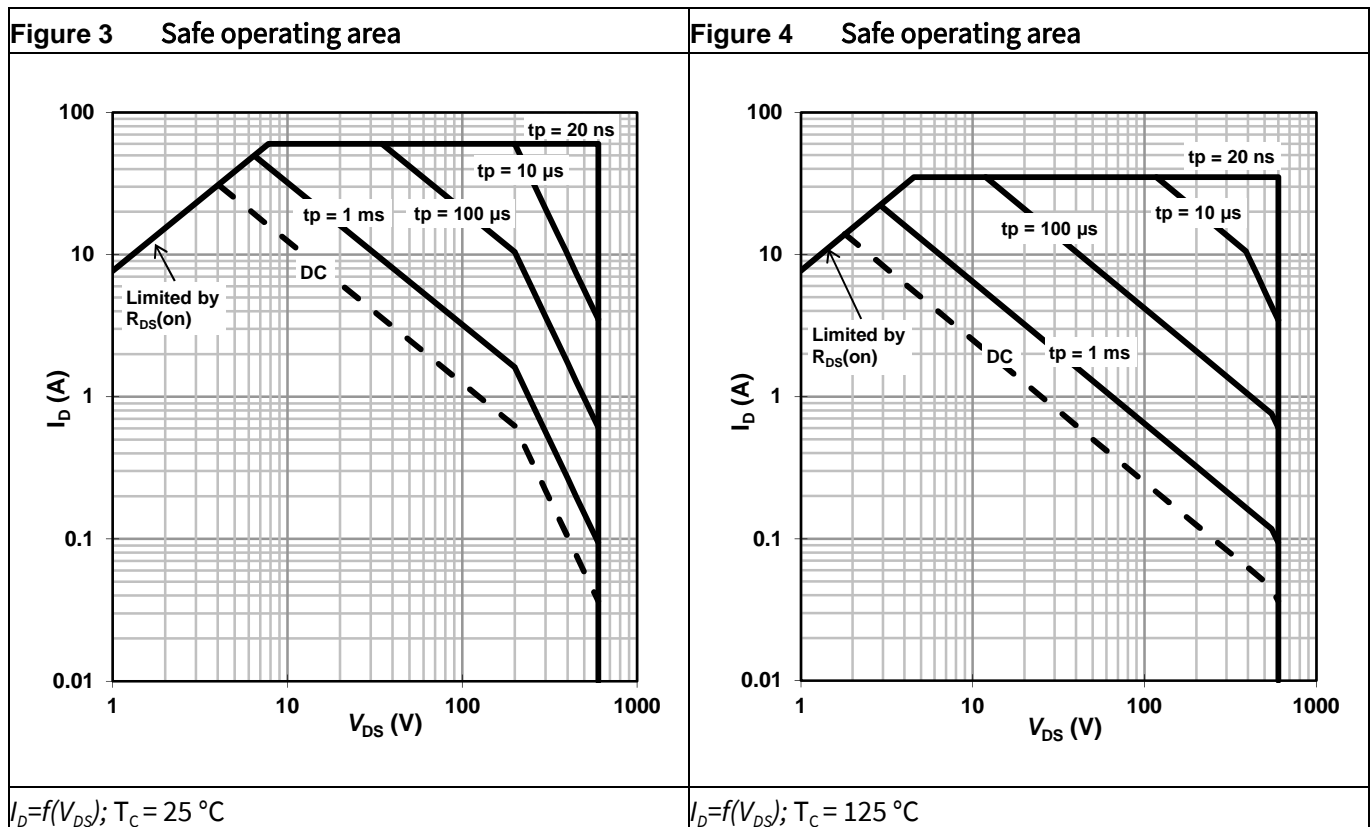
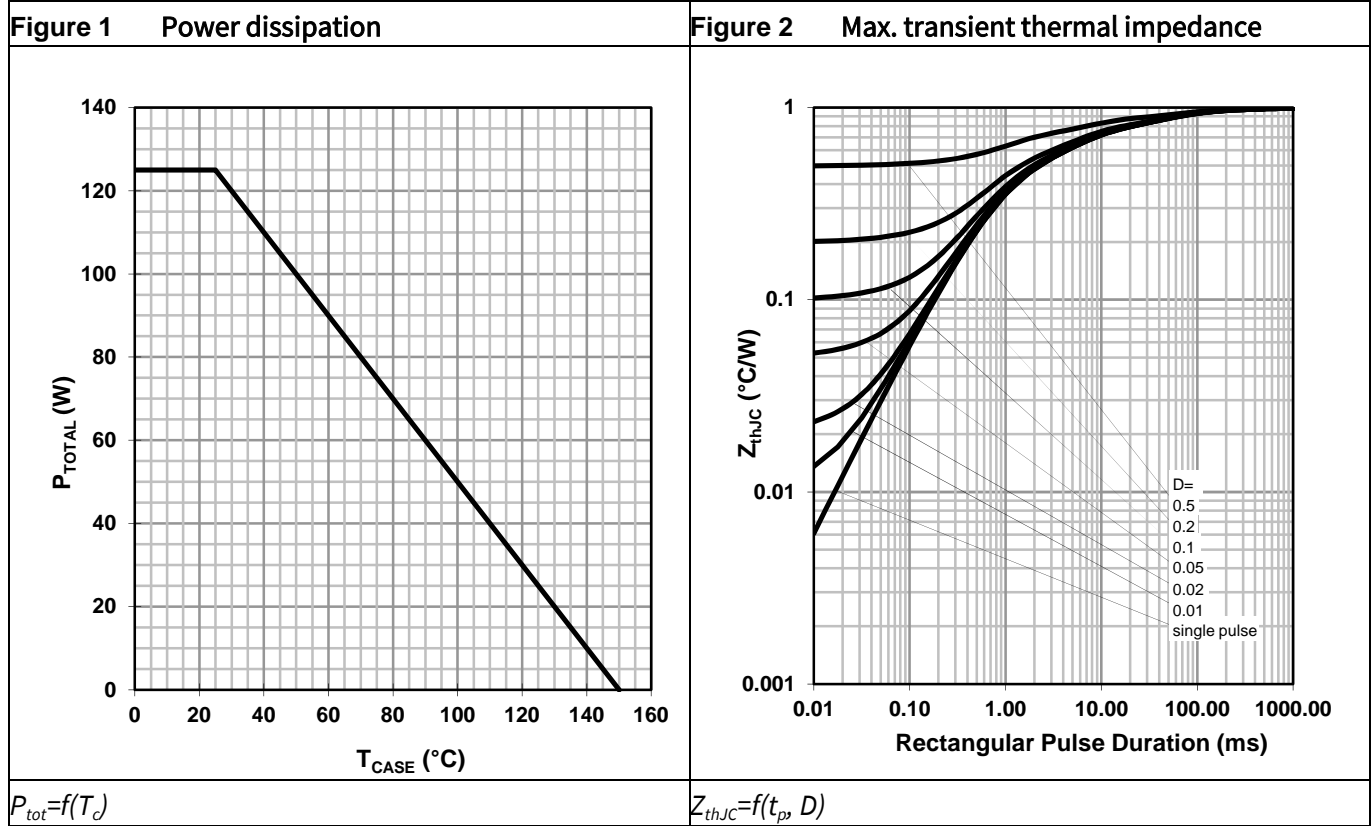
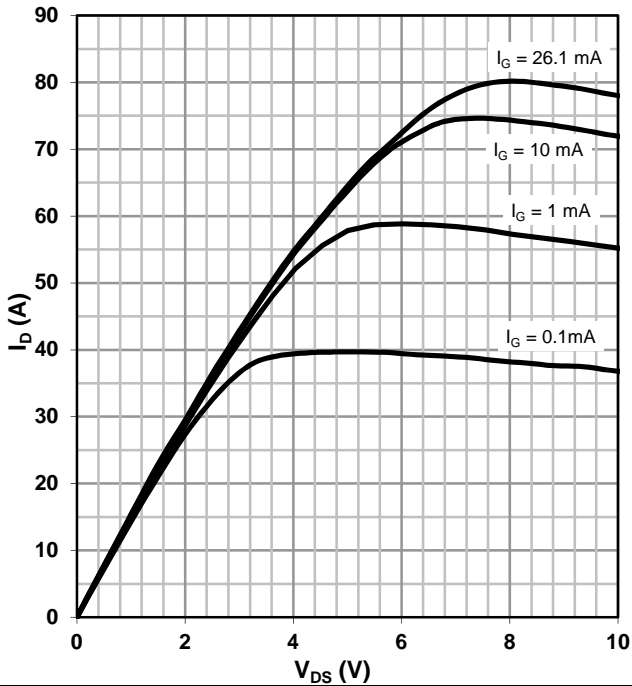
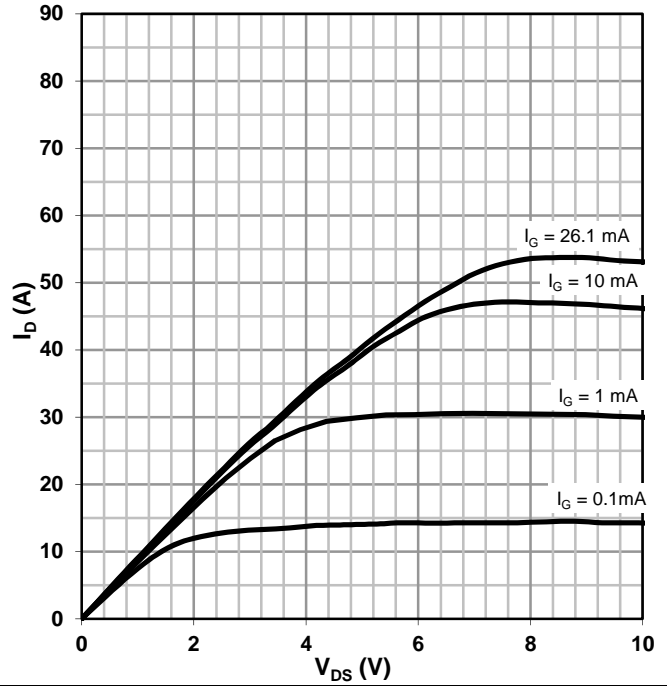


Figure 5 Typ. output characteristics



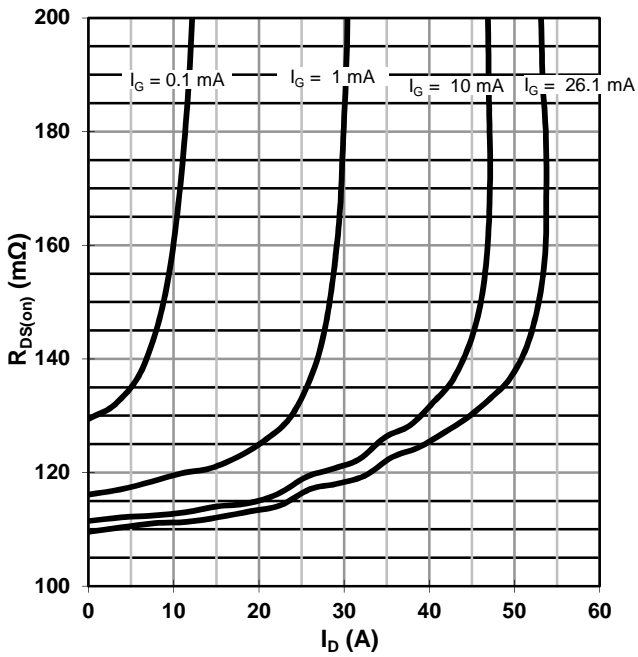
$I_D = f(V_{DS}, I_G); T_j = 25\text{ °C}$

Figure 6 Typ. output characteristics



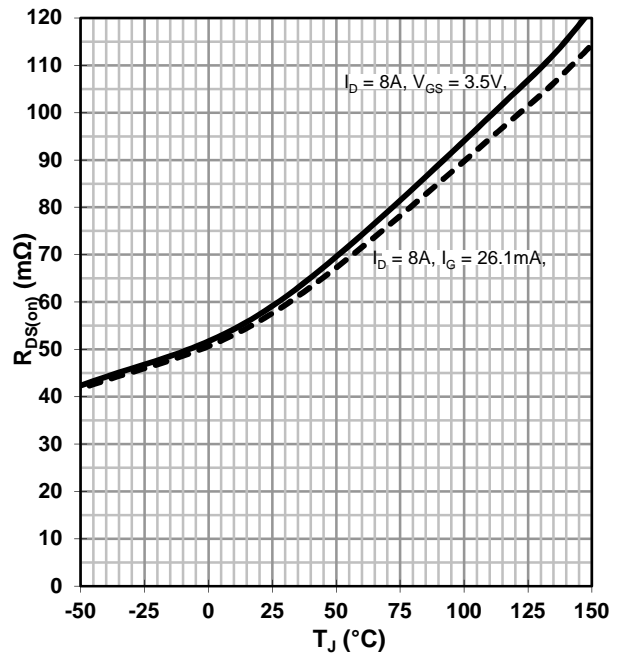
$I_D = f(V_{DS}, I_G); T_j = 125\text{ °C}$

Figure 7 Typ. Drain-source on-state resistance



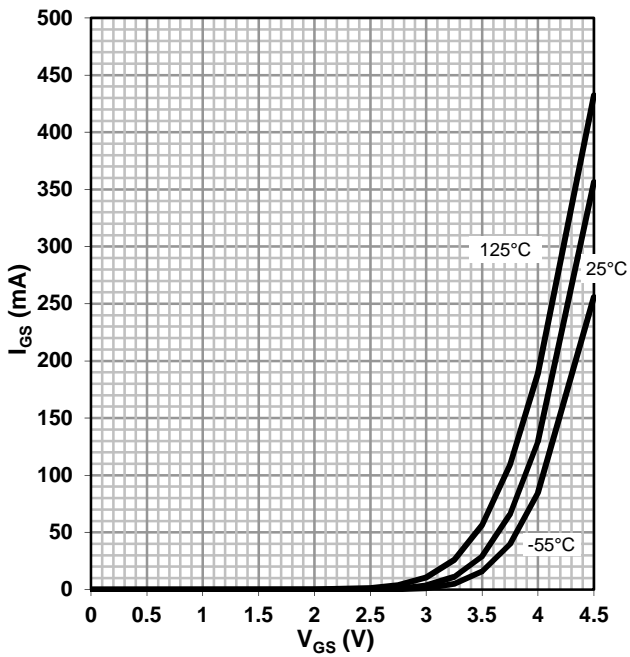
$R_{dson} = f(I_D, I_G); T_j = 125\text{ °C}$

Figure 8 Drain-source on-state resistance



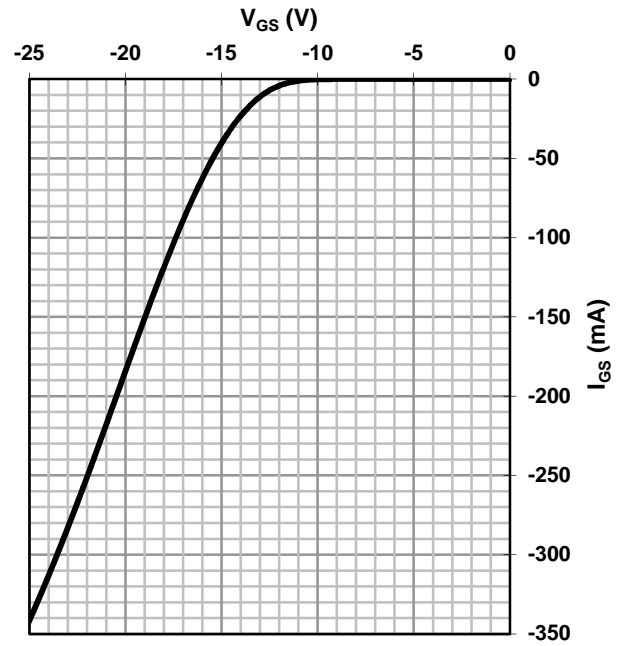
$R_{dson} = f(T_j); I_D = 8\text{ A}$

Figure 9 Typ. gate characteristics forward



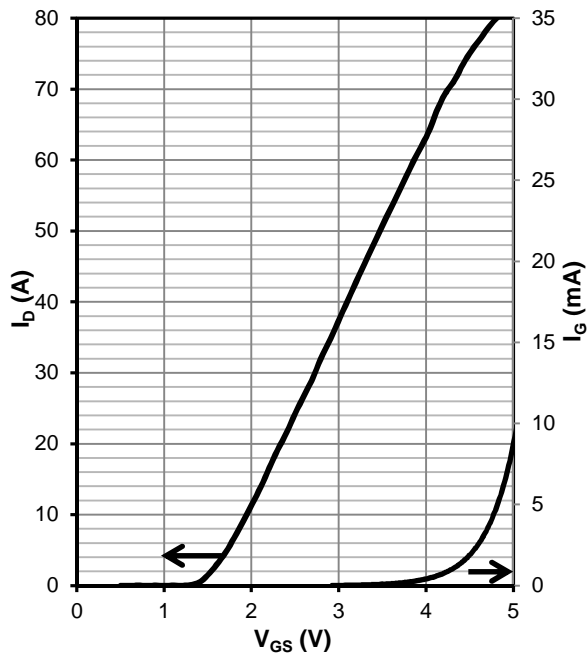
$I_{GS} = f(V_{GS}, T_j)$; open drain

Figure 10 Typ. gate characteristics reverse



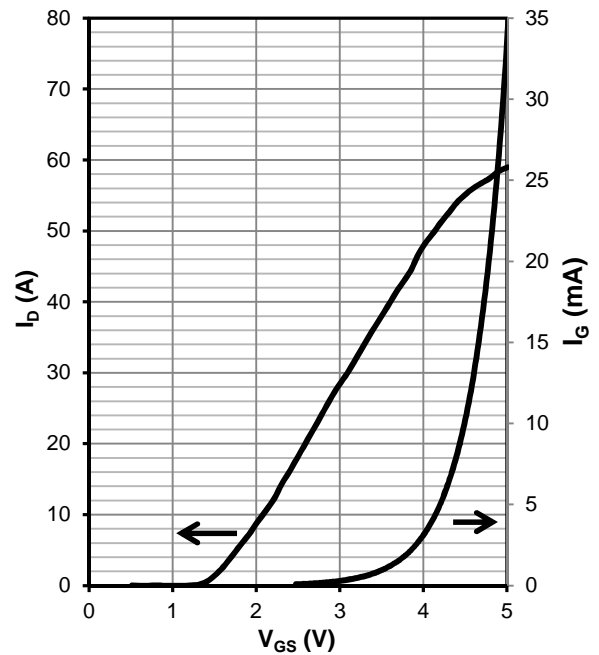
$I_{GS} = f(V_{GS})$; $T_j = 25^\circ\text{C}$

Figure 11 Typ. transfer characteristics



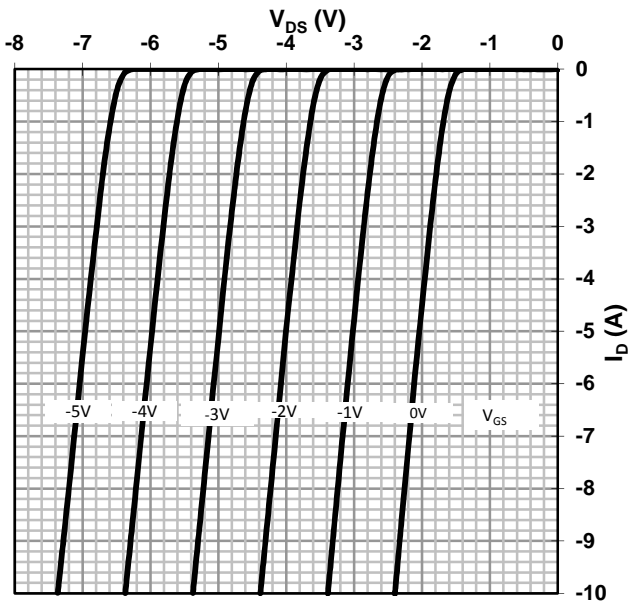
$I_D, I_G = f(V_{GS})$; $V_{DS} = 8\text{ V}$; $T_j = 25^\circ\text{C}$

Figure 12 Typ. transfer characteristics



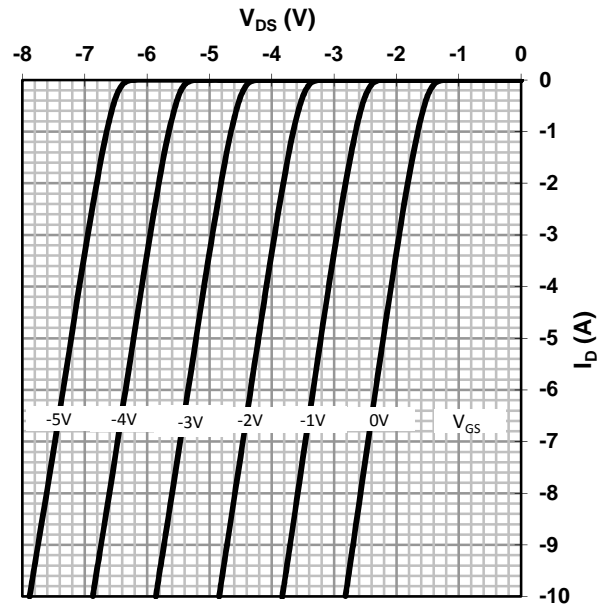
$I_D, I_G = f(V_{GS})$; $V_{DS} = 8\text{ V}$; $T_j = 125^\circ\text{C}$

Figure 13 Typ. channel reverse characteristics



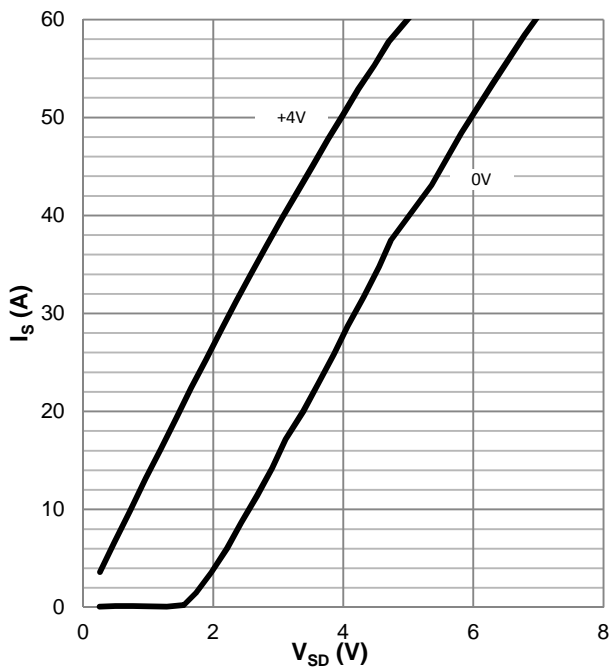
$V_{DS}=f(I_D, V_{GS}); T_j = 25\text{ °C}$

Figure 14 Typ. channel reverse characteristics



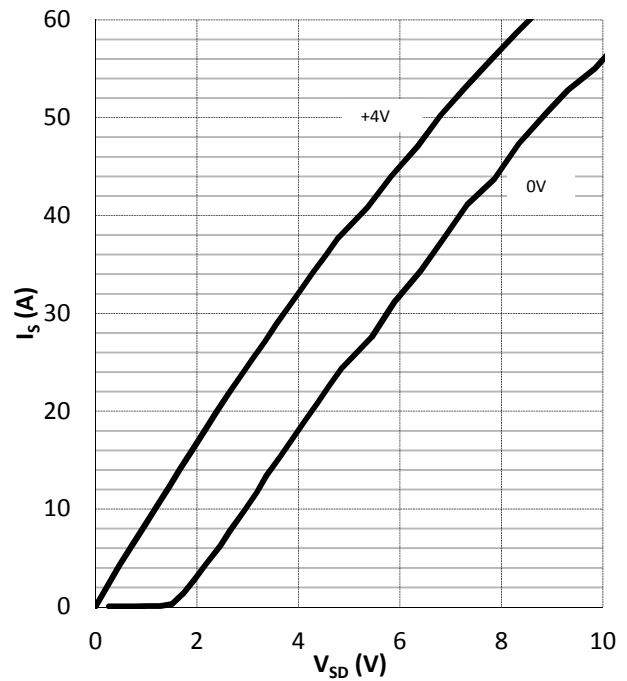
$V_{DS}=f(I_D, V_{GS}); T_j = 125\text{ °C}$

Figure 15 Typ. channel reverse characteristics



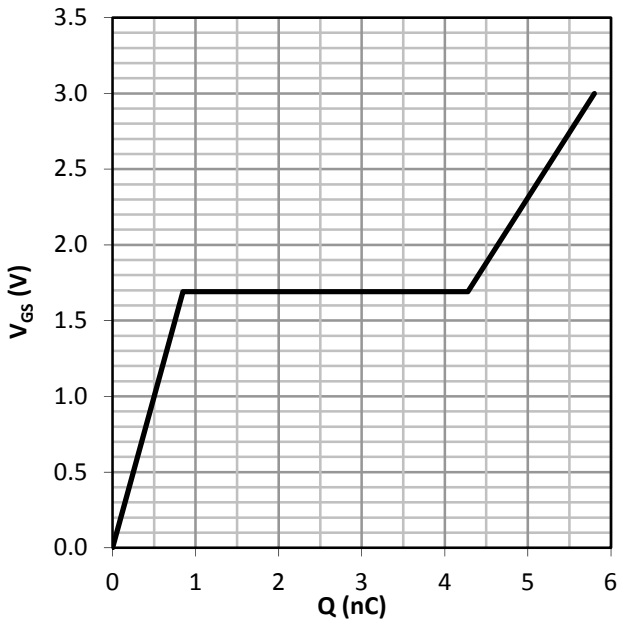
$I_D=f(V_{DS}, V_{GS}); T_j = 25\text{ °C}$

Figure 16 Typ. channel reverse characteristics



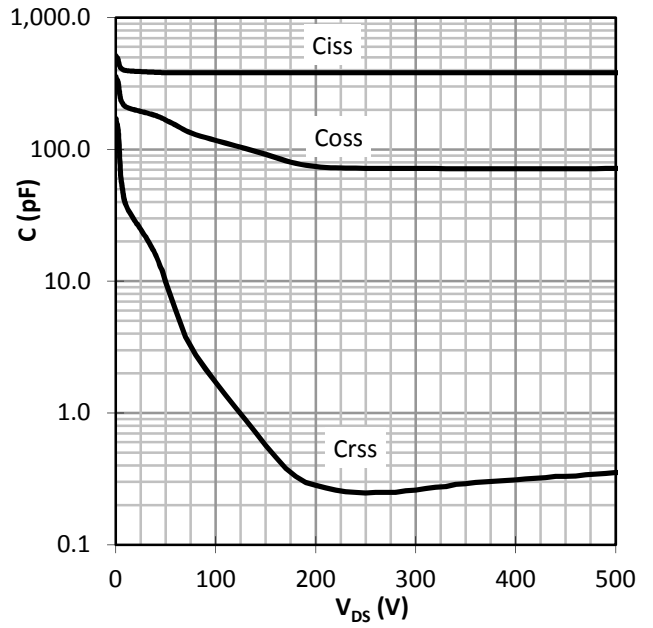
$I_D=f(V_{DS}, V_{GS}); T_j = 125\text{ °C}$

Figure 17 Typ. gate charge



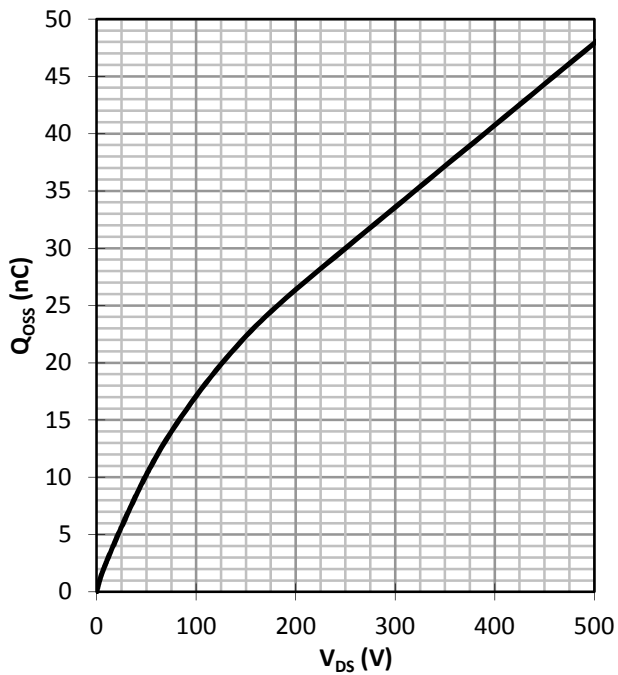
$V_{GS} = f(Q_G); V_{DCLINK} = 400\text{ V}; I_D = 8\text{ A}$

Figure 18 Typ. capacitances



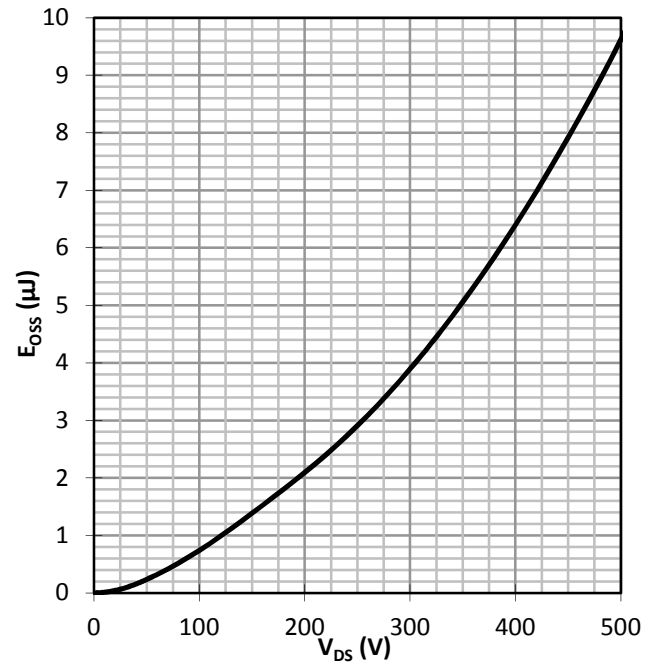
$C_{XSS} = f(V_{DS})$

Figure 19 Typ. output charge



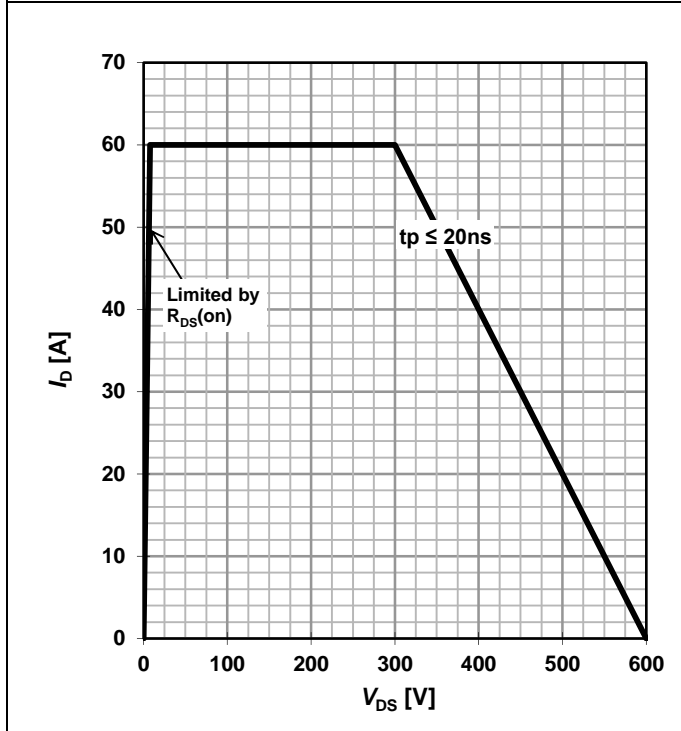
$Q_{OSS} = f(V_{DS})$

Figure 20 Typ. Coss stored Energy



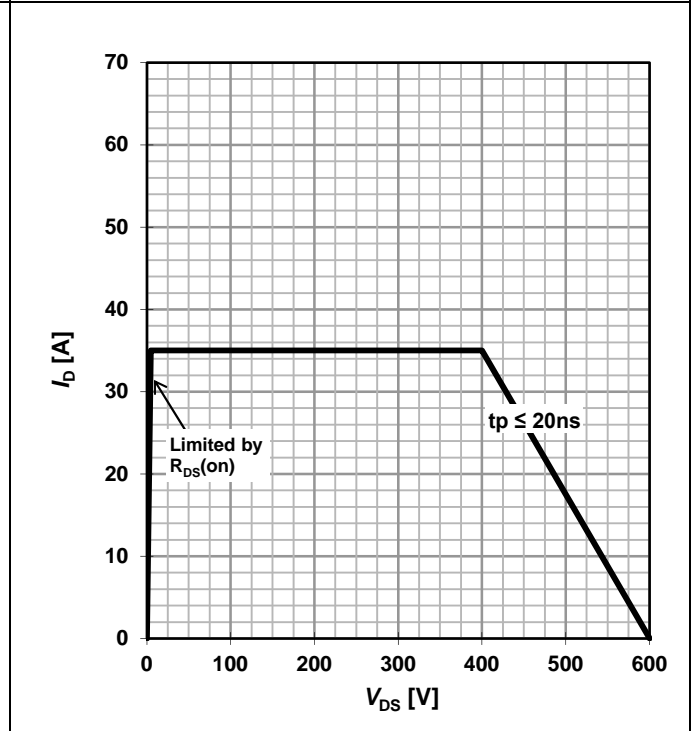
$E_{OSS} = f(V_{DS})$

Figure 21 Repetitive safe operating area¹



T_c = 25 °C; T_j ≤ 150 °C

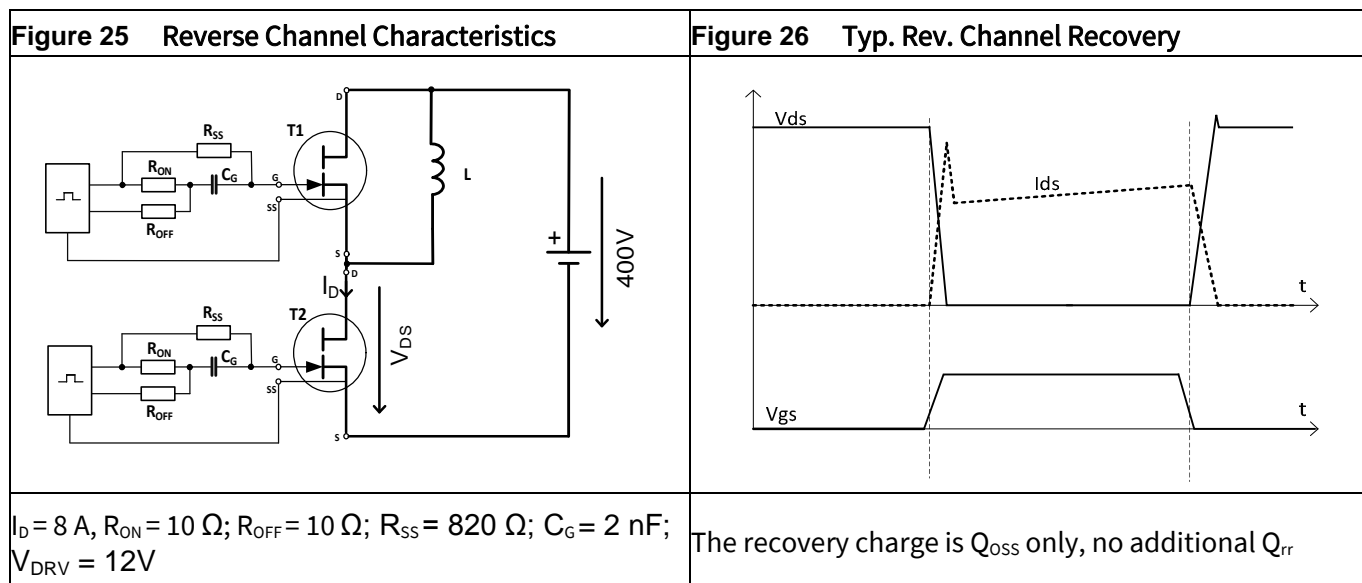
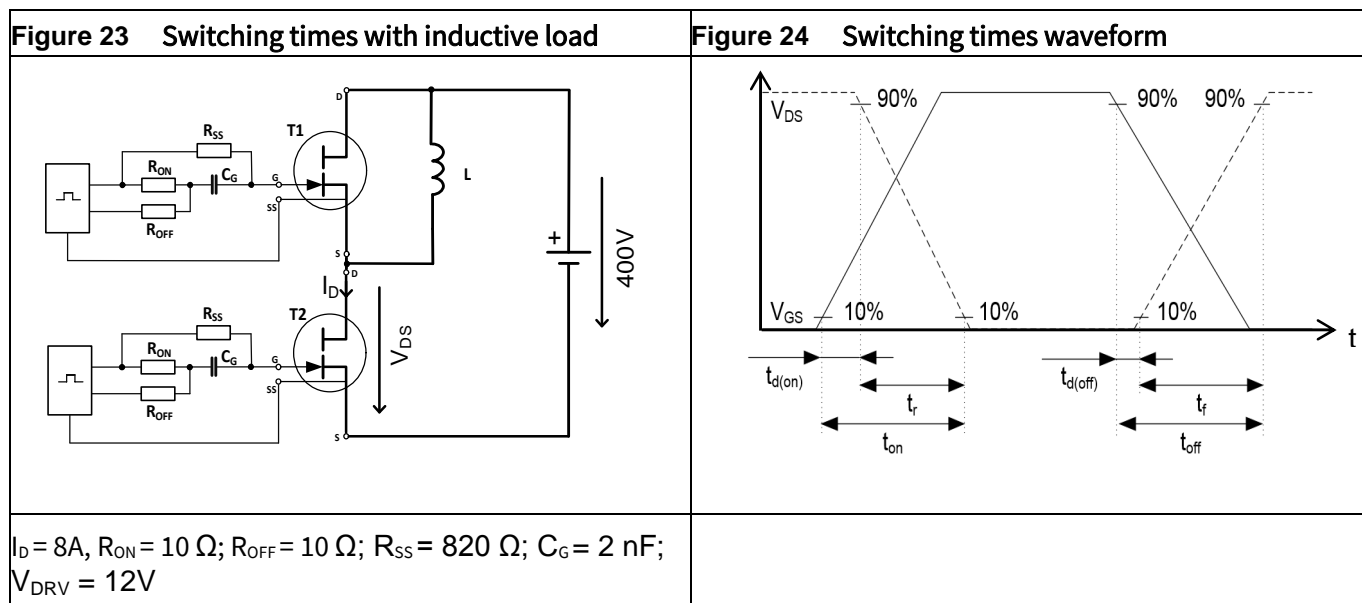
Figure 22 Repetitive safe operating area¹



T_c = 125 °C; T_j ≤ 150 °C

¹ Parameter is influenced by rel-requirements. Please contact the local Infineon Sales Office to get an assessment of your application.

5 Test Circuits



6 Package Outlines

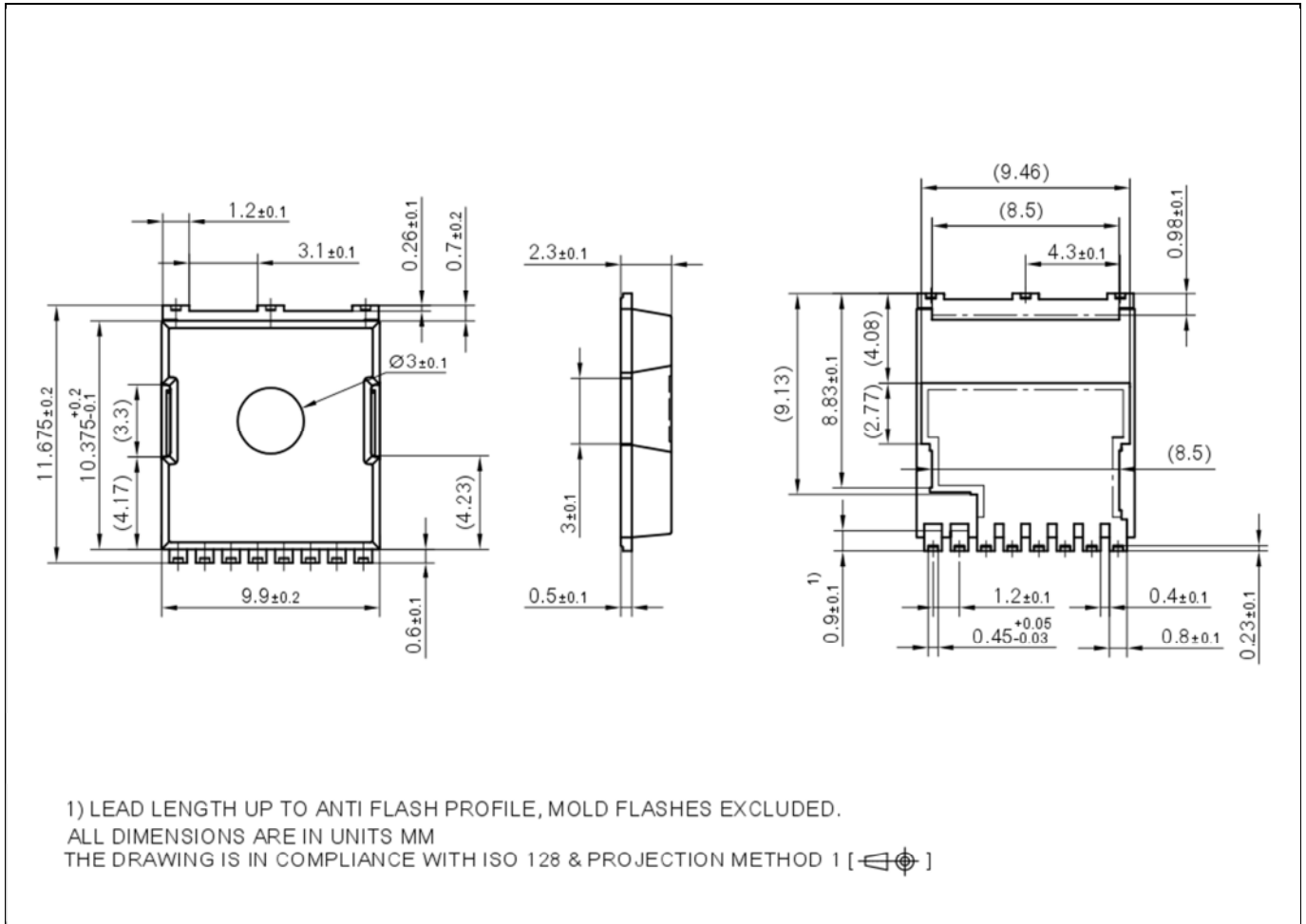


Figure 27 PG-HSOF-8 Package Outline, dimensions (mm)

7 Revision History

Major changes since the last revision

Revision	Date	Description of change
2.0	2018-04-24	Final version release

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